

# **Modify Record:**

版次	新版本	旧版本	修改单位	修改内容	
2019-06-01	1.0	NA	研发部	新文件制成(因工程产品,故 RD 开头)	
2020-06-11	1. 1	1.0	研发部	增加典型应用电路图	
2020-06-24	1.2	1.1	研发部	增加 EMSOP8 封装	
2020-07-31	1.3	1.2	研发部	增加应用信息,增加EN 耐压信息	
2020-08-17	1.4	1.3	研发部	更新典型应用电路、增加PSRR	
2020-09-28	1.5	1.4	研发部	增加SOP8脚位图	
2020-11-06	1.6	1.5	研发部	增加T0252脚位图	
2021-08-05	1. 7	1.6	研发部	增加S0T89-3导电胶脚位图	



### General Description(产品描述)

SE86XX series is designed for powersensitive applications. It includes a precision and high voltage input stage, an ultra-low-power bias current branch, and results in a ultra-low-power and low-dropout linear regulator.

The SE86XX operates from an input voltage of V<sub>OUT</sub>+1V to 65V, consumes only 1.8µA of quiescent current, and offers 1% initial accuracy and low dropout voltage, 70mV typical at 10mA.

SE86XX is a fixed output LDO with available has available voltages at 3.3V and 5.0V.

Although designed primarily as fixed voltage regulators, the device can be used with external resistors to obtain variable output voltages. The typical such application circuit, along with the needed calculations for accurate output voltages, are attached on the following page.

Other features include short-circuit protection and thermal shutdown.

### Features(产品特性)

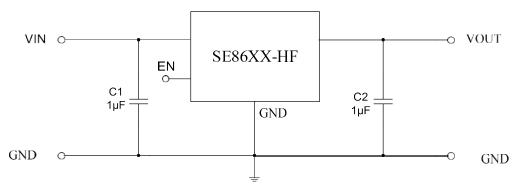
- Ultra Low Quiescent Current: 1.8uA(Typ.)
- Wide Operating Voltage: V<sub>OUT</sub>+1V to 65V (max Vin can be up to 80V)
- High output current: ≥200mA
- System startup with no overshoot
- Short circuit protection is designed with no overshoot
- Low Dropout Voltages:
  - 70mV@10mA
  - 700mV@100mA
- High Accuracy Output Voltage: ±2%
  - Accuracy can be 1% for special orders
- Excellent power / load transientresponse
- Low temperature coefficient: ±100ppm/°C
- Thermal and Short-Circuit Protection
- With EN pin
- Available Packages: SOT23-3, SOT23-5, SOT89, EMSOP8, SOP8, TO252

## Applications(产品应用)

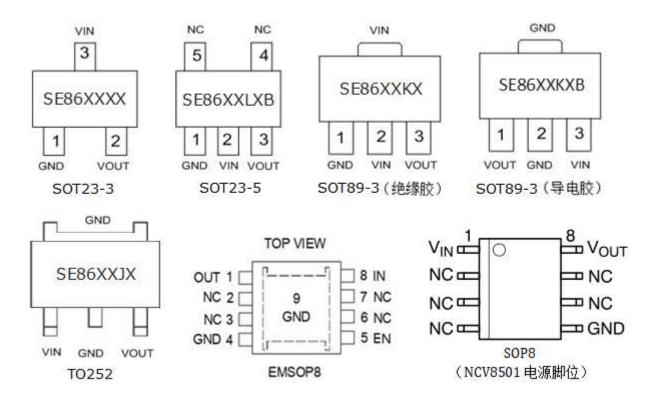
- Battery-powered equipment
- Smoke detector and sensor
- Microcontroller Applications
- Smart electric meter



### Typical Application (典型应用电路)



### Pin Configuration (管脚排列)



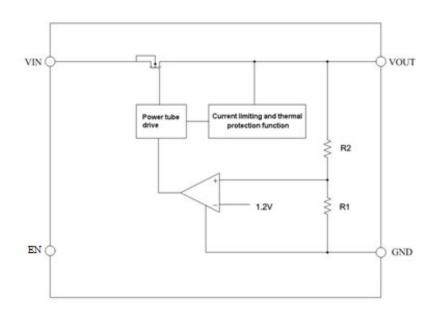
注: 芯片上对应的标识为成品名称,只作为下单参考。

### Pin Description (管脚功能描述)

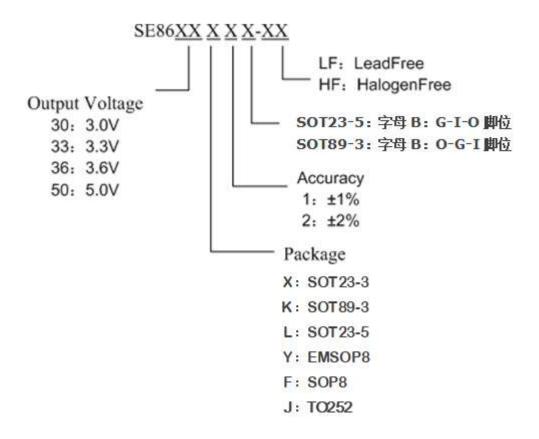
Pin Name	Pin Function Description
VIN	In put pin
VOUT	Out put pin
GND	Ground pin
EN	Enable pin
NC	No connection



### Functional Block Diagram (功能框图)



### Ordering Information(订货信息)





## Absolute Maximum Ratings(最大额定参数)

Symbol	Parameter	Value	Units	
V <sub>IN</sub>	Input Supply Voltage	80		
EN	Enable Voltage	80		
V <sub>OUT</sub> GND	Output Voltage TO GND	6	V	
VoutVIN	Output Voltage TO VIN	-75		
T <sub>A</sub>	Operating Temperature	-40105		
T <sub>STG</sub>	Storage Temperature	-40150		
TJ	Maximum Junction Temperature	150	- °C	
$T_{LEAD}$	Lead Temperature (Soldering) 10 seconds	260		
		165(SOT89)		
$ heta_{\sf JA}$	Thermal Resistance, Junction-to-Ambient –	280(SOT23-3)	□ °C/W	
		270(SOT23-5)	C/VV	
		180(SOP8)		
		85(TO252)		
		750(SOT89)		
$P_D$	Power Consumption	446(SOT23-3)	\^/	
		465(SOT23-5)	mW	
		700(SOP8)		
		1300(TO252)		
Electrostatic	Human Body Model(HBM)	4	kV	
discharge rating	Charged Device Model (MM)	100	V	

Note: Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

## Recommended Operating Conditions(推荐工作条件)

Symbol	Parameter	Maximum	Units
V <sub>IN</sub>	Input Supply Voltage	60	V
T <sub>A</sub>	Operating Temperature	-2085	°C
T <sub>LEAD</sub>	Lead Temperature (Soldering) 10 seconds	260	°C



# Electrical Characteristics(电气参数)

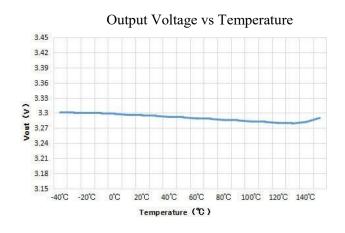
 $(~TA=25^{\circ}~C,~CIN=1uF,~VIN=VOUT+1.0V,~COUT=10\mu F,~unless~otherwise~noted)$ 

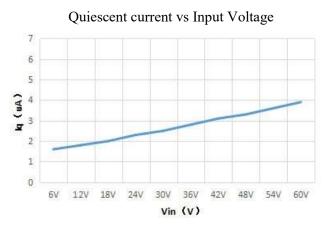
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IN</sub>	Input Supply Voltage		2.8		60	V
V <sub>OUT</sub>	Output Voltage Accuracy	I <sub>OUT</sub> =10mA	-1%		1%	V
			-2%		2%	V
IQ	Quiescent Current	V <sub>IN</sub> =6V~60V		1.8	4	μA
I <sub>OUT</sub>	Output Current			200		mA
		$I_{OUT}$ =10mA $\Delta V_{OUT}$ = - $V_{OUT}$ *2%		70		mV
$V_{DROP}$	Dropout Voltage	I <sub>OUT</sub> =100mA ΔV <sub>OUT</sub> = - V <sub>OUT</sub> *2%		700		mV
$V_{LR}$	Load Regulation	1mA ≤ I <sub>OUT</sub> ≤ 100mA		20		mV
V <sub>SR</sub>	Line Regulation	$I_{OUT}$ =1mA, $V_{IN}$ =( $V_{OUT}$ +1V) to 60V		0.2		%/V
PSRR	Power Supply Rejection Ratio	Vin=12V , Iout=10mA F=1Khz,Vout=3.3V	_	70	_	dB
$V_{ENH}$	Enable High Level	Enabled	1		_	V
V <sub>ENL</sub>	Enable Low Level	Disabled			0.4	V
I <sub>EN</sub>	EN Current	EN=0~V <sub>IN</sub> (R <sub>EN</sub> =100K)		1		μA
I <sub>LIMIT</sub>	Current Limit			250		mA
T <sub>SHDN</sub>	Thermal Protection			150		$^{\circ}$
ТО	Output Voltage	I <sub>OUT</sub> =10mA				100
TC <sub>VOUT</sub>	Temperature Coefficient	-40°C≤T <sub>AMB</sub> ≤100°C		-17		ppm/℃

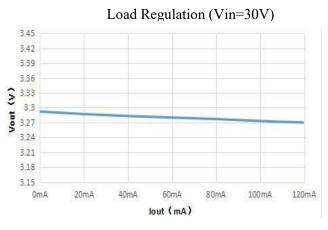


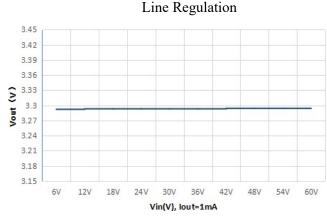
# Typical Performance Characteristics(典型性能特性)

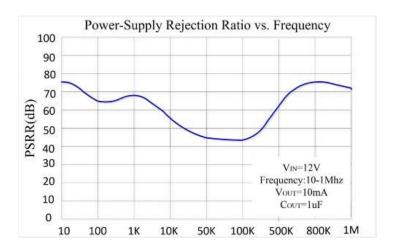
( TA=25° C, CIN=1uF, VIN=VOUT (3.3V) +1.0V, COUT=10µF, unless otherwise noted)





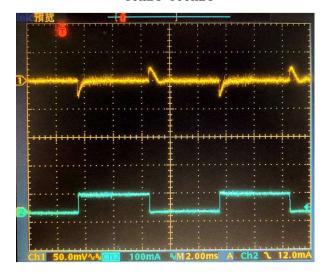




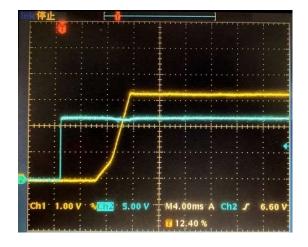




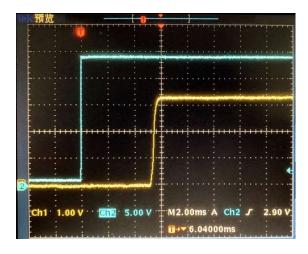
Load Transient (Vin=12V)  $10mA\sim100mA$ 



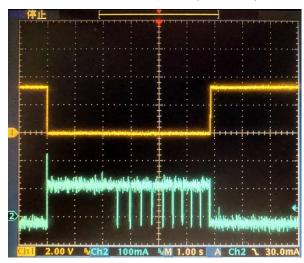
EN OFF**→**ON



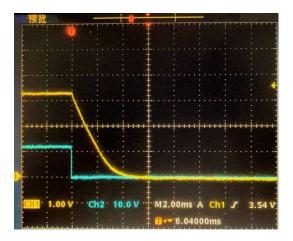
VCC Power ON



Short-Circuit and OTP (Vin=24V)



EN ON→ OFF (No Load) Discharge





### **APPLICATION INFORMATION**

#### **INPUT CAPACITOR**

An input ceramic capacitor of  $1\mu F$  is required between the VIN and GND pin. The capacitor shall be placed as close as possible to VIN pin, and the wide copper trace is also recommended.

#### **OUTPUT CAPACITOR**

The recommended is 10 uF ceramic capacitor. The minimum capacitance for stable and correct operation is  $1 \mu \text{F}$ . The higher the value of this output capacitor, the lower the ripple during the operations. The output capacitor should be placed as close to the Output Pin as possible. The wide copper trace is recommended.

#### **NO-LOAD STABILITY**

The SE86XX will remain stable and in regulation with no external load.

#### FOLD-BACK SHORT-CIRCUIT PROTECTION

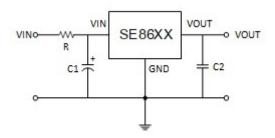
When short-circuit occurs, SE86XX will fold back the short-circuit currents to a pre-determined lower level, This will reduce excessive heat in otherwise large current conditions. This feature provides another level of protection to IC itself and also the whole system.

#### **EN Functions**

EN is Hi-Z internally. EN must be connected to either to Vcc (through a resistor) or GND externally, if SOT23-5 package is used. If left floating, the Vout is unknown.

#### IN-RUSH CURRENT AND VOLTAGE

The following figure shows a typical application circuit for the SE86XX devices. Please keep in mind that in-rush current can push up the Vin overshoot by as much as 50%. For example, when Vin=50V, the in-rush caused spike voltage can be as high as 75V. Therefore the voltage rating of Cin needs to be higher than 50% of the application.

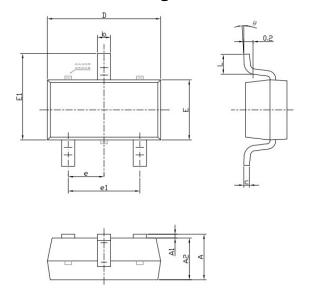


In live insertion application, it is suggested that R, C1 are selected as following:

- $1.C1=10\mu F \sim 100\mu F$  ceramic or electrolytic capacitor with maximum voltage greater than 80V, R=0
- 2. If the average current is known, for example at 10mA, then for an input voltage of 55V, the C1=1 $\mu$ F ~ 10 $\mu$ F ceramic or electrolytic with maximum voltage greater than 80V and R=2K $\Omega$  in the type of 1206 at 1/4W rating can be selected.

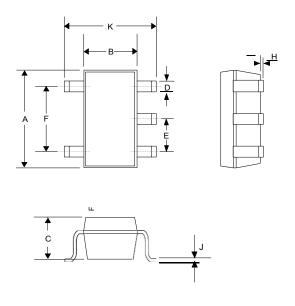


# **Outline Drawing for SOT-23-3**



0	Dimensions	In Millimeters	Dimensions in Inche	
Symbol	Mln	Max MIn		Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950	(BSC)	0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0"	8

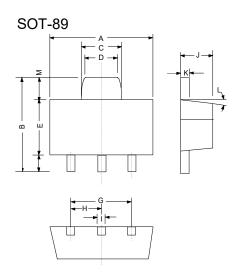
# **Outline Drawing for SOT-23-5**



DIMENSIONS						
DIM	INCHES		MM			
	MIN	MAX	MIN 2.80 1.50 0.90 0.35 - -	MAX		
Α	0.110	0.120	2.80	3.05		
В	0.059	0.070	1.50	1.75		
С	0.036	0.051	0.90	1.30		
D	0.014	0.020	0.35	0.50		
E	-	0.037	-	0.95		
F	-	0.075	-	1.90		
Н	-	0.006	-	0.15		
J	0.0035	0.008	0.090	0.20		
K	0.102	0.118	2.60	3.00		

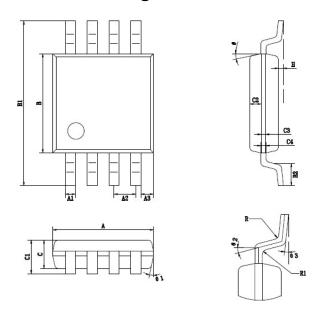


## **Outline Drawing for SOT-89**



DIM ENSIO NS						
DIM <sup>N</sup>	INC	HES	ММ			
ואוט	MIN	M AX	MIN	M AX		
Α	0.173	0 .181	4.400	4 .600		
В	0.159	0 .167	4.050	4 .250		
С	0.067	0 .075	1.700	1 .900		
D	0.051	0 .059	1.300	1 .500		
Е	0.094	0 .102	2.400	2 .600		
F	0.035	0 .047	0.890	1 .200		
G	0.118REF		3.00	REF		
Н	0.059REF		1.50	REF		
I	0.016	0 .020	0.400	0 .520		
J	0.055	0 .063	1.400	1 .600		
K	0.014	0 .016	0.350	0 .410		
L	10 °	10 °TYP 10 °TYP		TYP		
М	0.028	REF	0.70	REF		

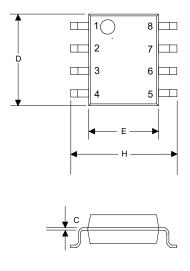
# **Outline Drawing for EMSOP8**

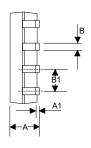


标准尺寸	最小(mm)	最大(==)	标准	最小(mm)	最大(mm)
A	2. 90	3. 10	C3	0.	152
A1	0. 3	OTYP	C4	0.	172
A2	0.6	5TYP	H	0.02	0. 15
AS	0. 3	75TYP	θ	12° TYP4	
В	2.90	3. 10	<del>0</del> 1	12	° TYP4
B1	4. 70	5. 10	0 2	14	* TYP
B2	0. 50	0.70	0 3	0,	' ~ 6°
С	0.75	0.96	R	0.	15TYP
C1	L	1. 10	R1	0.	15TYP
C2	0. 3	7			



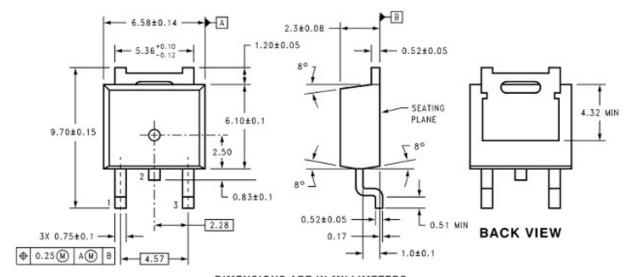
## **Outline Drawing for SOP8**





DIMENSIONS						
DIM <sup>N</sup>	INC	HES	MM			
ואווט	MIN	MAX	MIN	MAX		
Α	0.0532	0.0688	1.35	1.75		
A1	0.0040	0.0098	0.10	0.25		
В	0.0130	0.0200	0.33	0.51		
B1	0.050 BSC		1.27 BSC			
С	0.0075	0.0098	0.19	0.25		
D	0.1890	0.1968	4.80	5.00		
Н	0.2284	0.2440	5.80	6.20		
Е	0.1497	0.1574	3.80	4.00		

## **Outline Drawing for TO252**



DIMENSIONS ARE IN MILLIMETERS

3-Lead TO-252 Package



### 联系方式:

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